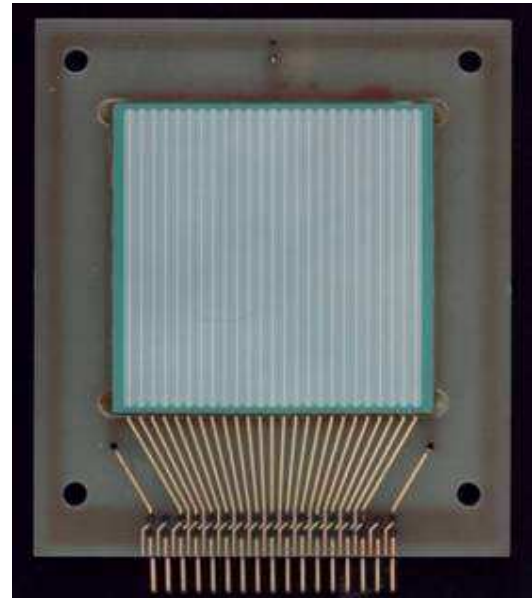


**SPECIALIST DETECTORS FOR NUCLEAR PHYSICS**

SILICON DETECTOR TYPE:	TOTALLY DEPELTED SILICON MICROSTRIP DETECTOR WITH OVER VOLTAGE OPERATION.	
TECHNOLOGY:	4 INCH SILICON	
N <sup>o</sup> of ELEMENTS:	25	
N <sup>o</sup> of OUTPUTS:	25	
ELEMENT ACTIVE LENGTH:	50 mm	
TOTAL ACTIVE WIDTH:	50 mm	
ELEMENT SEPARATION:	25 $\mu$ m	
ELEMENT PITCH:	2 mm	
THICKNESS:	65 $\mu$ m, 140 $\mu$ m, 300 $\mu$ m, and 500 $\mu$ m	
RISE TIME:	20 ns maximum	
ELEMENT CAPACITANCE:	185 – 25 pF subject to thickness	
NOMINAL INTERSTRIP RESISTANCE:	100 M $\Omega$	
ALPHA RESOLUTION	Junction 55 KeV FWHM maximum Ohmic 75 KeV FWHM maximum	
MAXIMUM NOISE PER ELEMENT ( $\mu$ s T.C):	20 KeV	
METALLISATION: CONTACTS	Aluminum 3000 $\text{\AA}$ 5% metallisation on the active area element 100 % metallisation on back	
STANDARD PACKAGE:	PCB 90 x 80 mm <sup>2</sup> Connections via soldering wires or spectra strip 801-075 Bonding wire-protected with epoxy resin to prevent user damage. Options: Total overcoat with moisture protection resin against dirty and high humidity environments.	
MINIMUM ACCEPTANCE LEVEL:	100 % elements operational when assembled based on 95% of addressed microstrip elements meeting the above specifications.	
SPECIFICATION IMPROVEMENTS:	Closer specification on the above parameters available an request	
BIASING:	Active area	Negative
	Substrate	Positive



QUALITY ASSURANCE :ISO9001

